DONG GUAN JIN SI LAI ELECTROIC CO., LTD

2SC3199

NPN SILICON TRANSISTOR

FEATURES

Power dissipation

P_{CM}: 400 mW (Tamb=25℃)

Collector current

I_{CM}: 150 mA

Collector-base voltage

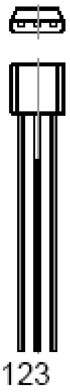
$V_{(BR)CBO}$: 50 V

Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to +150℃

TO-92S

1. EMITTER
2. COLLECTOR
3. BASE



ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=100μA, I_E=0	50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=1mA, I_B=0	50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=100μA, I_C=0	5			V
Collector cut-off current	I_{CBO}	V_{CB}=50V, I_E=0			0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=5V, I_C=0			0.1	μA
DC current gain	$h_{FE(1)}$	V_{CE}=6V, I_C=2mA	70		700	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=100mA, I_B=10mA		0.1	0.25	V
Transition frequency	f_T	V_{CE}=10V, I_C=1mA	80			MHz
Collector output capacitance	C_{ob}	V_{CB}=10V, I_E=0, f=1MHz		2.0	3.5	pF
Noise figure	NF	V_{CE}=6V, I_C=0.1mA, f=1KHZ, Rg=10KΩ		1.0	10	dB
h_{FE} Linearity		h_{FE}(0.1mA)/h_{FE}(2mA)		0.95		

CLASSIFICATION OF $h_{FE(1)}$

Rank		Y	GR	
Range		120-240	200-400	

东莞市金思来电子有限公司　　地址：广东省东莞市东城区石井工业区
业务：陈生 手机：13602373598 TEL：0769-22361548 26878796 QQ:739136338
http://www.dgjinsilai.com E-mail：jinsilai86@163.com